QSI LASER DIODE SPECIFICATIONS FOR APPROVAL

Customer :.					
Model: QL68I6S-A/	/B/C				
Signature of App	roval				
Approved by					
Checked by					
Issued by					
Approval by Customer					



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WWW.QSILaser.com

QL68I6S-A/B/C

InGaAIP Laser Diode

Quantum Semiconductor International Co., Ltd.

Ver. 1 MAR. 2011

♦ OVERVIEW

QL68i6S-A/B/C is a MOCVD grown 0.68μm band InGaAIP laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 30mW for optoelectronic devices such as Industrials.

APPLICATION

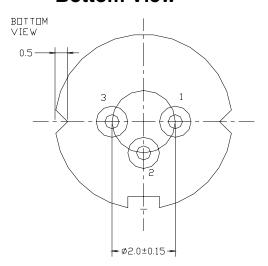
- Industrials
- Laser Module

♦ FEATURES

- Visible Light Output : $\lambda p = 685 \text{ nm}$ - Optical Power Output : 30mW CW

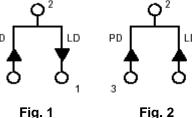
Package Type : TO-18 (5.6mmφ)
 Built-in Photo Diode for Monitoring Laser Diode

♦ ELECTRICAL CONNECTIONBottom View



Pin Configuration

А	LD cathode, PD anode (Fig. 1)		
В	LD , PD anode (Fig. 2)		
С	LD anode, PD cathode (Fig. 3)		





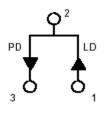


Fig. 3 QL68I6SC



♦ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	Р	35	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	−10 ~ +60	°C
Storage Temperature	Tstg	−40 ~ +85	°C

♦ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

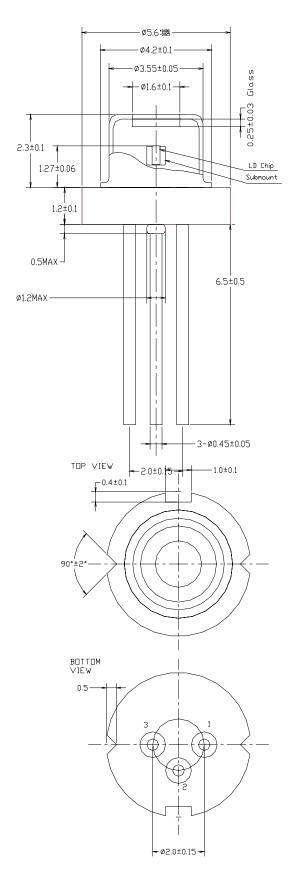
Items	Symbols	Min.	Тур.	Max.	Unit	Condition
Optical Output Power	Po	-	30	-	mW	-
Threshold Current	Ith	-	28	60	mA	-
Operating Current	lop	-	59	140	mA	Po=30mW
Operating Voltage	Vop	2	2.2	3	V	Po=30mW
Lasing Wavelength	λр	670	683	700	nm	Po=30mW
Beam Divergence	θΠ	8	11	14	deg	Po=30mW
	θ⊥	16	19	25	deg	Po=30mW
Beam Angle	Δθ	-	-	±2.0	deg	Po=30mW
	Δθ ⊥	-	-	±2.5	deg	Po=30mW
Monitor Current	lm	0.05	0.4	2.5	mA	Po=30mW
Astigmatism	As			8	μ m	
Optical Distance	ΔΧ, ΔΥ, ΔΖ	-	-	±60	μ m	-

NOTICE: QL68I6S-A/B/C to be operated on APC

The above product specifications are subject to change without notice.



PACKAGE DIMENSION





♦PACKING

